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PNP Darlington Power Silicon Transistor

Qualified per MIL-PRF-19500/527

Qualified Levels: JAN, JANTX, and JANTXV

DESCRIPTION

This high speed PNP transistor is rated at -10 amps and is military qualified up to the JANTXV level. This TO-204AA isolated package features a 180 degree lead orientation.



TO-204AA (TO-3) Package

Important: For the latest information, visit our website http://www.microsemi.com.

FEATURES

- JEDEC registered 2N6648 through 2N6650
- JAN, JANTX, and JANTXV qualifications are available per MIL-PRF-19500/527
- RoHS compliant versions available (commercial grade only)

APPLICATIONS / BENEFITS

- Military and other high reliability applications
- High frequency response
- TO-204AA case with isolated terminals

MAXIMUM RATINGS @ $T_A = +25$ °C unless otherwise noted

Parameters/Test Conditions	Symbol	Value	Unit	
Junction and Storage Temperature	T_J and T_{STG}	-65 to +175	°C	
Thermal Resistance Junction-to-Cas	R _{eJC}	1.76	°C/W	
Collector-Emitter Voltage	2N6648	V_{CEO}	-40	V
	2N6649		-60	
	2N6650		-80	
Collector-Base Voltage	2N6648	V_{CBO}	-40	V
	2N6649		-60	
	2N6650		-80	
Emitter-Base Voltage		V_{EBO}	-5	V
Total Power Dissipation	@ $T_A = +25 {}^{\circ}C^{(1)}$ @ $T_C = +25 {}^{\circ}C^{(2)}$	P_T	5.0	W
	@ $T_C = +25 {}^{\circ}C^{(2)}$		85	
Base Current		I _B	-0.25	Α
Collector Current		I _C	-10	Α

Notes: 1. Derate linearly 33.3 mW/°C above T_A > +25 °C.

2. Derate linearly 567 mW/°C above $T_{C} > +25$ °C.

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MECHANICAL and PACKAGING

- CASE: Industry standard TO-204AA (TO-3), hermetically sealed, 0.040 inch diameter pins
- FINISH: Solder dipped tin-lead over nickel plated alloy 52 or RoHS compliant matte-tin plating. Solderable per MIL-STD-750 method 2026.
- POLARITY: PNP (see <u>schematic</u>)
- MOUNTING HARDWARE: Consult factory for optional insulator and sheet metal screws
- WEIGHT: Approximately 15 grams
- See package dimensions on last page.

table)

JAN 2N6648 (e3) Reliability Level JAN = JAN Level JANTX = JANTX Level JANTXV = JANTXV Level Blank = Commercial Blank = Commercial JEDEC type number (see Electrical Characteristics

SYMBOLS & DEFINITIONS				
Symbol	Definition			
I _B	Base current: The value of the dc current into the base terminal.			
Ic	Collector current: The value of the dc current into the collector terminal.			
I _E	Emitter current: The value of the dc current into the emitter terminal.			
T _C	Case temperature: The temperature measured at a specified location on the case of a device.			
V _{CB}	Collector-base voltage: The dc voltage between the collector and the base.			
V _{CBO}	Collector-base voltage, base open: The voltage between the collector and base terminals when the emitter terminal is open-circuited.			
V _{CC}	Collector-supply voltage: The supply voltage applied to a circuit connected to the collector.			
V _{CEO}	Collector-emitter voltage, base open: The voltage between the collector and the emitter terminals when the base terminal is open-circuited.			
V _{CE}	Collector-emitter voltage: The dc voltage between the collector and the emitter.			
V _{EB}	Emitter-base voltage: The dc voltage between the emitter and the base.			
V _{EBO}	Emitter-base voltage, collector open: The voltage between the emitter and base terminals with the collector terminal open-circuited.			



ELECTRICAL CHARACTERISTICS @ T_A = +25 °C unless otherwise noted

Characteristics	Symbol	Min.	Max.	Unit			
OFF CHARACTERISTICS							
Collector-Emitter Breakdown Voltage I _C = -200 mA	2N6648 2N6649 2N6650	$V_{(BR)CEO}$	-40 -60 -80		V		
Collector-Emitter Breakdown Voltage I_C = -200 mA, R_{BB} = 100 Ω	2N6648 2N6649 2N6650	$V_{(BR)CER}$	-40 -60 -80		V		
Collector-Emitter Cutoff Current $V_{CE} = -40 \text{ V}$ $V_{CE} = -60 \text{ V}$ $V_{CE} = -80 \text{ V}$	2N6648 2N6649 2N6650	I _{CEO}		-1.0	mA		
Collector-Emitter Cutoff Current $V_{CE} = -40 \text{ V}, V_{BE} = 1.5 \text{ V}$ $V_{CE} = -60 \text{ V}, V_{BE} = 1.5 \text{ V}$ $V_{CE} = -80 \text{ V}, V_{BE} = 1.5 \text{ V}$	2N6648 2N6649 2N6650	I _{CEX}		10	μΑ		
Emitter-Base Cutoff Current V _{EB} = 5.0 V		I _{EBO}		-10	mA		
Collector-Emitter Cutoff Current $V_{CE} = -40 \text{ V}$ $V_{CE} = -60 \text{ V}$ $V_{CE} = -80 \text{ V}$	2N6648 2N6649 2N6650	I _{CBO}		-1.0	mA		
ON CHARACTERISTICS							
Forward-Current Transfer Ratio $I_C = -1.0 \text{ A}, V_{CE} = -3.0 \text{ V}$ $I_C = -5 \text{ A}, V_{CE} = -3.0 \text{ V}$ $I_C = -10 \text{ A}, V_{CE} = -3.0 \text{ V}$ $I_C = -10 \text{ A}, V_{CE} = -3.0 \text{ V}, T_A = -65 ^{\circ}\text{C}$		h _{FE}	300 1,000 100 200	20,000			
Collector-Emitter Saturation Voltage $I_C = -5.0 \text{ A}, I_B = -10 \text{ mA}$ $I_C = -10 \text{ A}, I_B = -0.1 \text{ mA}$		$V_{\text{CE}(\text{sat})}$		-2.0 -3.0	V		
Base-Emitter Voltage Non-saturated $V_{CE} = -3.0 \text{ V}, I_C = -5.0 \text{ A}$ $V_{CE} = -3.0 \text{ V}, I_C = -10 \text{ A}$		$V_{BE(on)}$		-2.8 -4.5	V		
DYNAMIC CHARACTERISTICS							
Magnitude of Common Emitter Small-Signa Forward Current Transfer Ratio $I_C = -1.0 \text{ A}, V_{CE} = -5.0 \text{ V}, f = 1.0 \text{ MHz}$	I Short-Circuit	h _{fe}	30	400			
Output Capacitance $V_{CB} = -10 \text{ V}, I_E = 0, 100 \text{ kHz} \le f \le 1 \text{ MHz}$		C _{obo}		300	pF		



ELECTRICAL CHARACTERISTICS @ T_C = 25 °C unless otherwise noted. (continued)

SWITCHING CHARACTERISTICS

Turn-On Time $V_{CC} = -30 \text{ V}, I_C = -5.0 \text{ A}; I_B = -20 \text{ mA}$	ton	2.5	μS
Turn-Off Time $V_{CC} = -30 \text{ V}, I_C = -5.0 \text{ A}; I_{B1} = I_{B2} = -20 \text{ mA}$	t _{off}	10	μS

SAFE OPERATING AREA (See Figures 1 and 2 and MIL-STD-750, Test Method 3053)

DC Tests $T_C = +25 \, ^{\circ}C$, t = 1 second, 1 Cycle **Test 1**

 $V_{CE} = -8.5 \text{ V}, I_{C} = -10 \text{ A}$

Test 2

 $V_{CE} = -25 \text{ V}, I_{C} = -3.4 \text{ A}$

Test 3

 $V_{CE} = -40 \text{ V}, I_{C} = -0.9 \text{ A} (2N6648)$

 $V_{CE} = -60 \text{ V}, I_{C} = -0.3 \text{ A} (2N6649)$

 $V_{CE} = -80 \text{ V}, I_{C} = -0.14 \text{ A} (2N6650)$



SAFE OPERATING AREA

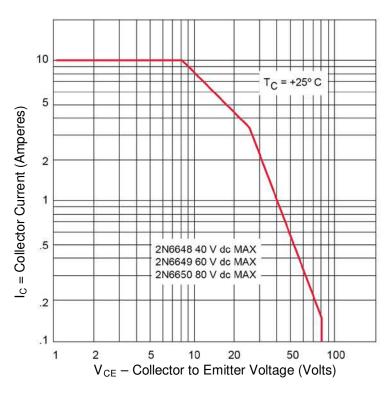


FIGURE 1

Maximum Safe Operating Graph (continuous dc)

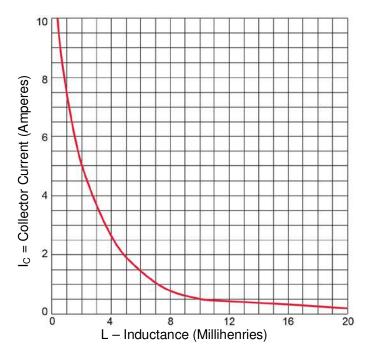
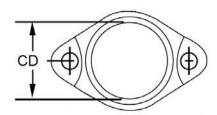
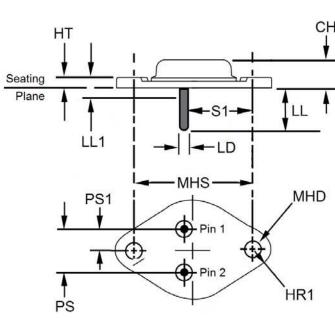


FIGURE 2
Safe Operating Area for Switching Between Saturation and Cutoff (unclamped inductive load)



PACKAGE DIMENSIONS





	Dimensions				
Ltr	Inches		Millimeters		Notes
	Min	Max	Min	Max	
CD	-	0.875	-	22.23	
CH	0.250	0.450	6.35	11.43	
HR	0.495	0.525	12.57	13.34	
HR1	0.131	0.188	3.33	4.78	
HT	0.050	0.135	1.52	3.43	
LD	0.038	0.043	0.97	1.09	
LL	0.312	0.500	7.92	12.70	
LL1	-	0.050	-	1.27	
MHD	0.151	0.161	3.84	4.09	
MHS	1.177	1.197	29.90	30.40	
PS	0.420	0.440	10.67	11.18	3
PS1	0.205	0.225	5.21	5.72	3
S1	0.655	0.675	16.64	17.15	

NOTES:

- 1. Dimensions are in inches.
- 2. Millimeters are given for information only.
- 3. These dimensions should be measured at points 0.050 inch (1.27 mm) and 0.055 inch (1.40 mm) below seating plane. When gauge is not used measurement will be made at the seating plane.
- 4. The seating plane of the header shall be flat within 0.001 inch (0.03 mm) concave to 0.004 inch (0.10 mm) convex inside a 0.930 inch (23.62 mm) diameter circle on the center of the header and flat within 0.001 inch (0.03 mm) concave to 0.006 inch (0.15 mm) convex overall.
- 5. Mounting holes shall be deburred on the seating plane side.
- 6. Collector is electrically connected to the case.
- 7. In accordance with AMSE Y14.5M, diameters are equivalent to Φx symbology.

See schematic on next page



SCHEMATIC

